

SPEC SHEET (FOR REFERENCE)	SHEET No.	Rev.	Page.
	G05102A		1 of 1

TYPE : 6PT32B6N3T

CHIP SIZE	0.81 * 0.81 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	23,036 pcs

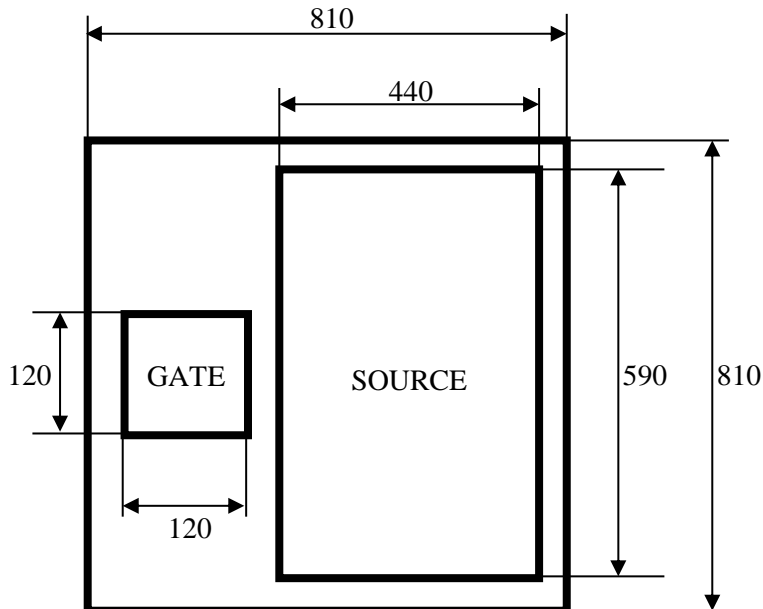
Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	60	V
Gate-source voltage	VGSS	±20	V
Drain Current (DC)	ID	1	A

* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			100	nA	VGS= ±20V VDS= 0V
2	IDSS			100	nA	VDS= 62V VGS= 0V
3	BVDSS	63			V	ID= 100uA
4	VTH	1.5		2.5	V	ID= 1mA
5	Ron 1		0.165	0.248	Ω	ID= 0.5A VGS= 10V
6	Ron 2		0.180	0.270	Ω	ID= 0.5A VGS= 7.5V
7	Ron 3		0.215	0.323	Ω	ID= 0.5A VGS= 5V
8	VSD			0.9	V	IS= 0.5A VGS= 0V



TENTATIVE

NOTE: